LDMOS S-Band radar pallet amplifier

Rev. 01 - 28 May 2010

Objective data sheet

1. Product profile

1.1 General description

200 W LDMOS amplifier pallet intended for radar applications in the 2.9 GHz to 3.3 GHz range.

Table 1. Typical performance

RF performance at $T_{case} = 25 \ ^{\circ}C$ in a common source class-AB test circuit.

Mode of operation	f	V _{DS}	P _{L(1dB)}	G _p	η _D	I _{Dq}
	(GHz)	(V)	(W)	(dB)	(%)	(mA)
class-AB; t_p = 300 $\mu s; \delta$ = 10 %	2.9 to 3.3	32	220	11	45	100

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- Excellent thermal stability
- Designed for broadband operation (2.9 GHz to 3.3 GHz)
- Matched to 50 Ω for ease of use
- Extreme low weight pallet (environmental friendly and easy to use)

1.3 Applications

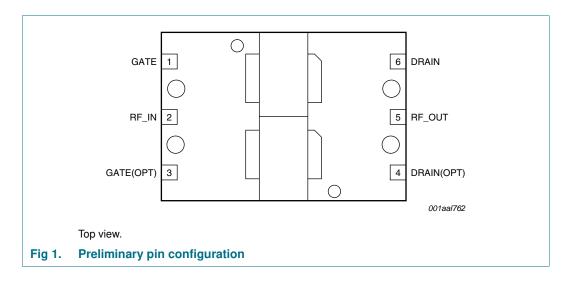
General S-Band radar applications



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2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2.	Pin description ^[1]	1
Symbol	Pin	Description
GATE	1	gate
RF_IN	2	RF input
GATE(OP	T) 3	optional gate
DRAIN(OF	PT) 4	optional drain
RF_OUT	5	RF output
DRAIN	6	drain

[1] The case is a source/ground connection.

3. Ordering information

Table 3. Orderin	Ordering information				
Type number	Package				
	Name	Description	Version		
BLS6G2933P-200	-	<tbd></tbd>	<tbd></tbd>		

BLS6G2933P-200

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4. Limiting values

Table 4. In accorda	Limiting values nce with the Absolute Maxin	num Rating System (IE	EC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-	60	V
V _{GS}	gate-source voltage		-	±11	V
I _D	drain current		-	66	А
T _{stg}	storage temperature		-40	+125	°C
Тj	junction temperature		-	200	°C

5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
Z _{th(j-h)}	transient thermal impedance from	$T_h = 25 \ ^{\circ}C; P_L = 200 \ W$		
	junction to heatsink	t_p = 300 μ s; δ = 10 %	[<u>1]</u> <tbd></tbd>	K/W
		t_p = 200 μ s; δ = 10 %	[<u>1]</u> <tbd></tbd>	K/W
		t_p = 100 μ s; δ = 10 %	[<u>1</u>] <tbd></tbd>	K/W

[1] Measured from junction to heatsink of the pallet.

6. Characteristics

Table 6. Characteristics per section

 $T_i = 25 \ ^{\circ}C$; unless otherwise specified.

]	· · ·					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 V; I_D = 1 mA$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_{D} = 360 \text{ mA}$	1.4	1.8	2.3	V
I _{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	10	μ A
I _{GSS}	gate leakage current	$V_{GS} = \pm 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	900	nA
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 10 \text{ A}$	-	13	-	S

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7. Application information

Table 7. Application information

RF performance in common source class-AB circuit; $T_h = 25 \ ^{\circ}C$; $t_p = 300 \ \mu$ s; $\delta = 10 \ ^{\circ}$; $I_{Dq} = 100 \ m$ A; $P_L = 215 \ W$; $Z_{th} = < tbd > K/W$; unless otherwise specified.

$V_{CC} \qquad supply voltage \qquad - \qquad 32 \qquad V_{cc}$ $t_p \qquad pulse duration \qquad - \qquad 300 \mu$ $\delta \qquad duty cycle \qquad - \qquad 10 \qquad - \qquad 300 \mu$ $\delta \qquad duty cycle \qquad - \qquad 10 \qquad - \qquad 900 000$	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t_p pulse duration300 μ δ duty cycle-10-% $P_{L(1dB)}$ output power at 1 dB gain compression-220-W G_p power gain1011-d η_D drain efficiency4045-% $P_{droop(pulse)}$ pulse droop power-0.10.3d Z_i input impedance-50- Ω	f	frequency		2.9	-	3.3	GHz
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	V _{CC}	supply voltage		-	-	32	V
$\begin{array}{cccc} P_{L(1dB)} & \mbox{output power at 1 dB gain compression} & - & 220 & - & W \\ G_p & \mbox{power gain} & 10 & 11 & - & d \\ \eta_D & \mbox{drain efficiency} & 40 & 45 & - & 92 \\ P_{droop(pulse)} & \mbox{pulse droop power} & - & 0.1 & 0.3 & d \\ Z_i & \mbox{input impedance} & - & 50 & - & 52 \\ Z_o & \mbox{output impedance} & - & 50 & - & 52 \end{array}$	tp	pulse duration		-	-	300	μS
$ \begin{array}{cccc} G_p & \mbox{power gain} & 10 & 11 & - & d \\ \eta_D & \mbox{drain efficiency} & dra$	δ	duty cycle		-	10	-	%
$ \begin{array}{cccc} G_p & \mbox{power gain} & 10 & 11 & - & d \\ \eta_D & \mbox{drain efficiency} & dra$	P _{L(1dB)}	output power at 1 dB gain compression		-	220	-	W
$\begin{array}{c cccc} P_{droop(pulse)} & pulse droop power & - & 0.1 & 0.3 & d \\ Z_i & input impedance & - & 50 & - & \Omega \\ Z_o & output impedance & - & 50 & - & \Omega \end{array}$		power gain		10	11	-	dB
Z_i input impedance-50- Ω Z_o output impedance-50- Ω	η_D	drain efficiency		40	45	-	%
Z_i input impedance-50- Ω Z_o output impedance-50- Ω	P _{droop(pulse)}	pulse droop power		-	0.1	0.3	dB
		input impedance		-	50	-	Ω
IRL input return loss10 - d	Zo	output impedance		-	50	-	Ω
	IRL	input return loss		-	-10	-	dB

7.1 Ruggedness in class-AB operation

The BLS6G2933P-200 is capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 100 mA; P_L = 215 W pulsed; t_p = 300 µs; δ = 10 %.

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8. Test information

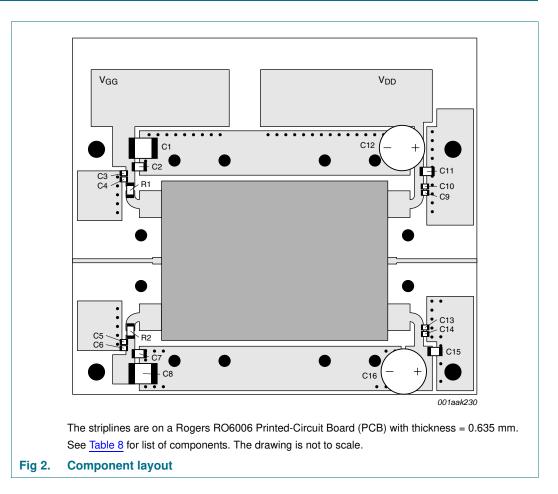


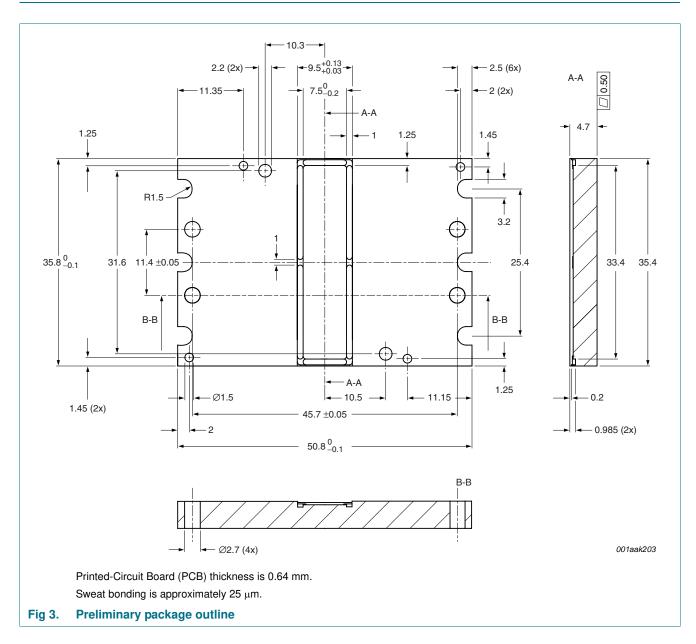
Table 8.List of componentsSee Figure 2 for component layout

See <u>Figure 2</u> for component layout.			
Component	Description	Value	Remarks
C1, C8	multilayer ceramic chip capacitor	47 μF	TDK
C2, C7, C11, C15	multilayer ceramic chip capacitor	100 pF	ATC100B
C3, C4, C5, C6, C9, C10, C13, C14	multilayer ceramic chip capacitor	33 pF	ATC100A
C12	electrolytic capacitor	680 μF	
C16	electrolytic capacitor	68 μF	
R1, R2	SMD resistor	33 Ω	thin film

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9. Package information



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10. Package outline

	uescripi	ion line												SOx
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							_	_						
							tb							
							LN							
						0	5		10) mm				
						0	5 sca	le	10) mm				
IMENS	SIONS (mr	n are the c	riginal	dimensic	ins)	0	5 sca	le	10) mm				
	SIONS (mr	n are the o	riginal	dimensic	ns)	0	5 sca	le	10) mm				
	SIONS (mr	n are the c	riginal	dimensio	ins)	0	5 sca	le	10) mm				
UNIT	SIONS (mr	n are the c	riginal	dimensic	ns)	0	sca	lle	10) mm				
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Fig 4. Package outline

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11. Abbreviations

Table 9.	Abbreviations
Acronym	Description
LDMOS	Laterally Diffused Metal Oxide Semiconductor
RF	Radio Frequency
S-Band	Short wave Band
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

12. Revision history

Table 10. Revision hist	e 10. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BLS6G2933P-200 v.1	20100528	Objective data sheet	-	-			

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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